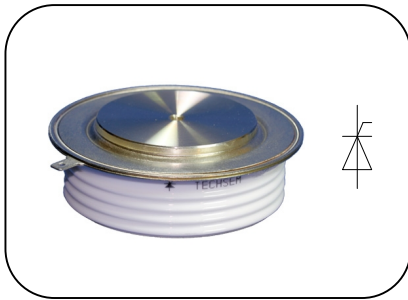


**Features**

Interdigitated amplifying gates
Fast turn-on and high di/dt
Low switching losses

Typical Applications

Inductive heating
Electronic welders
Self-commutated inverters

Part No. Y70KFE-KT60cT

$I_{T(AV)}$	2500A
V_{DRM}	800V~2000V
V_{RRM}	1000V~1800V
t_q	15~75μs

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T_J (°C)	VALUE			UNIT
					Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180 half sine wave 50Hz Double side cooled	$T_C=55^\circ\text{C}$	125			2500	A
V_{DRM}	Repetitive peak off-state voltage	$t_p=10\text{ms}$		125	800		2000	V
V_{RRM}	Repetitive peak reverse voltage				1000		1800	V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}		125			200	mA
I_{TSM}	Surge on-state current	10ms half sine wave		125			29	kA
I^2t	I^2t for fusing coordination	$V_R=0.6V_{RRM}$					4205	$10^3\text{A}^2\text{s}$
V_{TO}	Threshold voltage			125			1.10	V
r_T	On-state slope resistance						0.13	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=4000\text{A}$, $F=32\text{kN}$	$15 \leq t_q \leq 28$	25			2.20	V
			$29 \leq t_q \leq 50$				2.00	V
			$51 \leq t_q \leq 75$				1.80	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$		125			1000	V/μs
di/dt	Critical rate of rise of on-state current (Non-repetitive)	$V_{DM}=67\%V_{DRM}$, Gate pulse $t_r \leq 0.5\mu\text{s}$ $I_{GM}=1.5\text{A}$		125			1500	A/μs
Q_{rr}	Recovery charge	$I_{TM}=2000\text{A}$, $t_p=4000\mu\text{s}$, $di/dt=-20\text{A}/\mu\text{s}$, $V_R=100\text{V}$		125		750		μC
t_q	Circuit commutated turn-off time	$I_{TM}=2000\text{A}$, $t_p=4000\mu\text{s}$, $V_R=100\text{V}$ $dv/dt=30\text{V}/\mu\text{s}$, $di/dt=-20\text{A}/\mu\text{s}$		125	15		75	μs
I_{GT}	Gate trigger current	$V_A=12\text{V}$, $I_A=1\text{A}$		25	40		250	mA
V_{GT}	Gate trigger voltage				0.9		2.5	V
I_H	Holding current				20		1000	mA
I_L	Latching current						1000	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$		125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180 sine double side cooled Clamping force 32kN					0.012	C/W
$R_{th(c-h)}$	Thermal resistance case to heatsink						0.003	
F_m	Mounting force				30		40	kN
T_{vj}	Junction temperature				-40		125	°C
T_{stg}	Stored temperature				-40		130	°C
W_t	Weight					880		g
Outline	KT60cT							

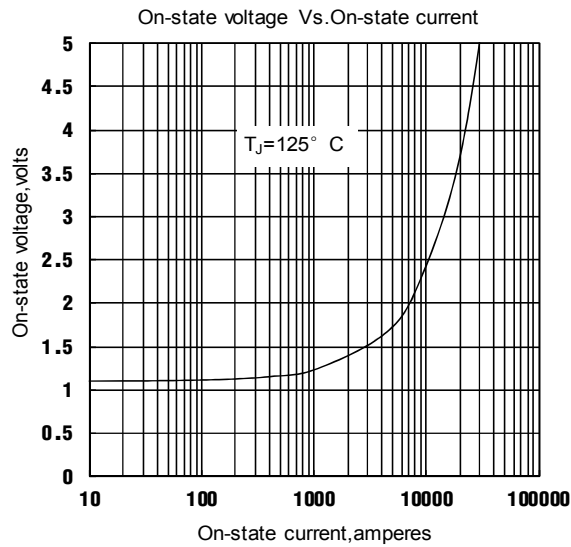


Fig.1

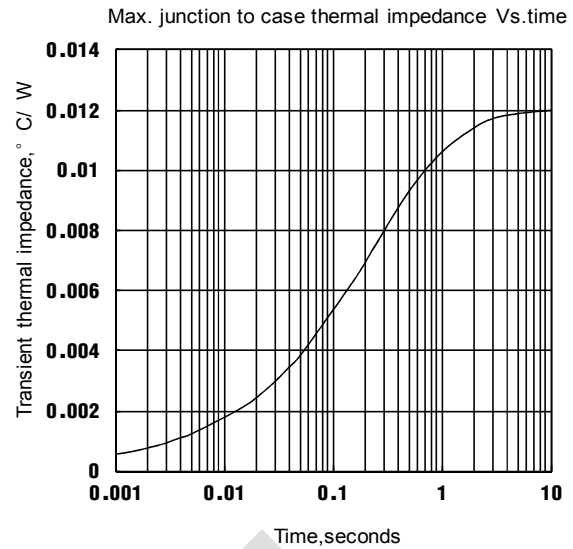


Fig.2

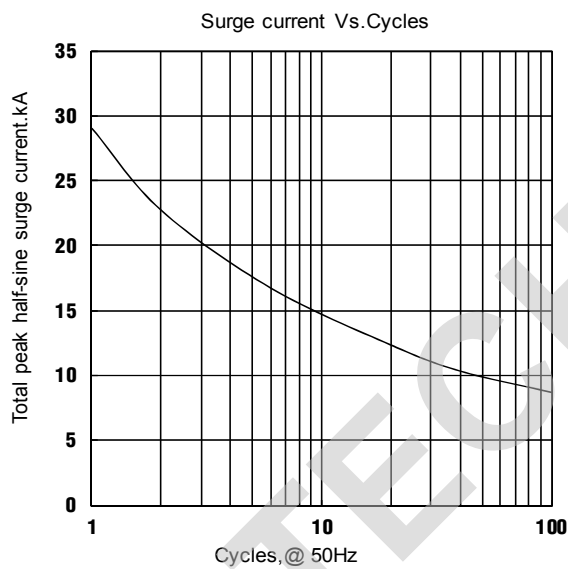


Fig.3

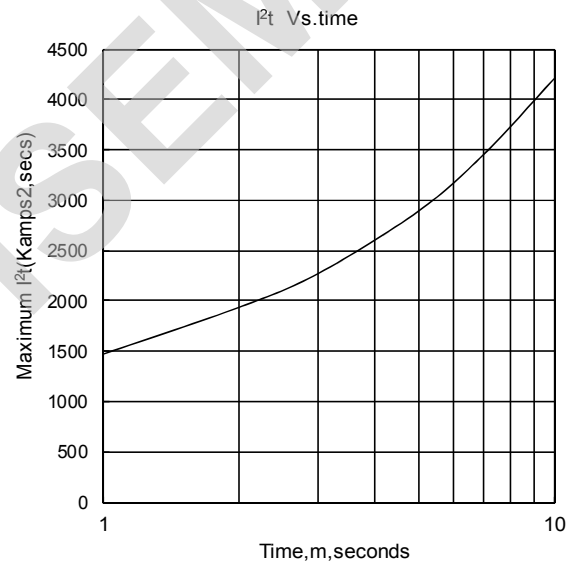


Fig.4

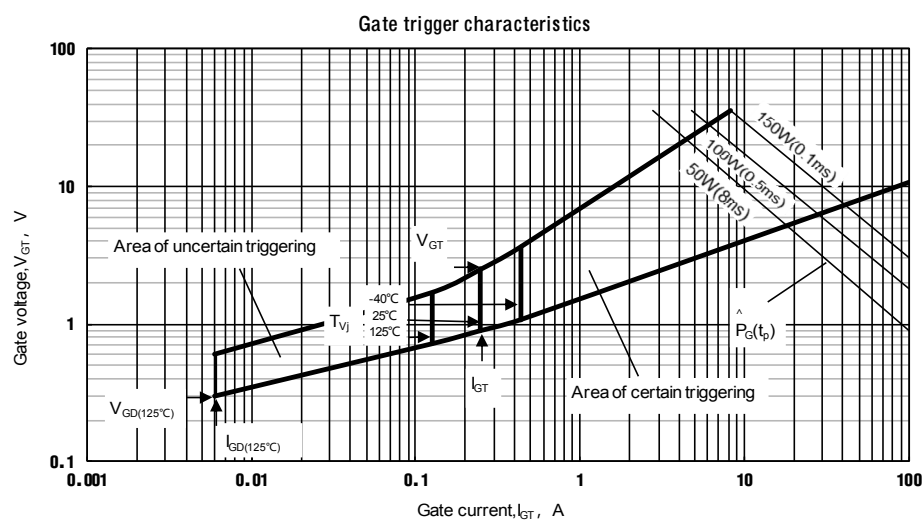
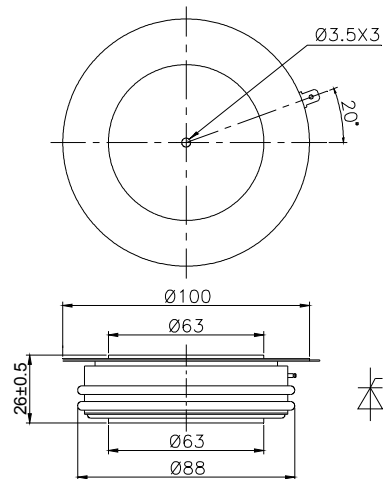


Fig.5

Outline:



TECHSEM reserves the right to change specifications without notice.